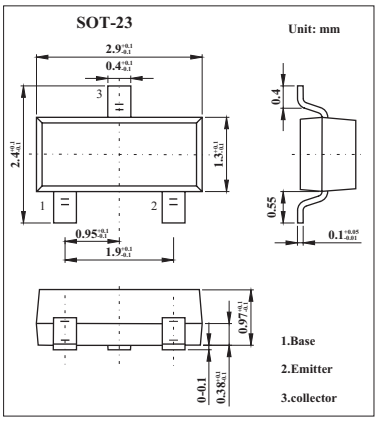
NPN Silicon Epitaxia

2SC3734



■ Features

● High speed : t_{stg}＜200ns.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	40	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	200	mA
Total power dissipation at 25℃ ambient temperature	P_T	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 30V, I_E=0			100	nA
Emitter cutoff current	I_{EBO}	V_{EB} = 3V, I_C=0			100	nA
DC current gain *	h_{FE}	V_{CE} = 1V , I_C = 10mA	75	200	300	
Collector-emitter saturation voltage *	$V_{CE(sat)}$	I_C = 50mA , I_B = 5mA		0.12	0.3	V
Base-emitter saturation voltage *	$V_{BE(sat)}$	I_C = 50mA , I_B = 5mA		0.8	0.95	V
Gain bandwidth product	f_T	V_{CE} = 20V , I_E = -10mA	300	510		MHz
Output capacitance	C_{ob}	V_{CB} = 5V , I_E = 0 , f = 1.0MHz		3.0	4.0	pF
Turn-on time	t_{on}	V_{CC} = 3V ,			70	ns
Storage time	t_{stg}	I_C = 10mA ,		100	200	ns
Turn-off time	t_{off}	I_{B1} = -I_{B2} = 1mA			250	ns

*. PW≤350μs,duty cycle≤2%

■ h_{FE} Classification

Marking	B22	B23	B24
hFE	75～150	100～200	150～300